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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

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Confirmation Number		Not yet assigned
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First Named Inventor		Heiji WATANABE
Art Unit		Not yet assigned
Examiner Name		Not yet assigned
Attorney Docket Number		Q85504

Sheet 1 of 1

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US			
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
		JP	2002-299607	A	10-11-2002	Toshiba Corp.	ABS
		JP	2002-164343	A	06-07-2002	Agere Systems Guardian Corp.	ABS
		JP	H10-242461	A	09-11-1998	Sony Corp.	ABS
		JP	2001-085427	A	03-30-2001	NEC Corp.	ABS
		JP	2001-257344	A	09-21-2001	Toshiba Corp.	ABS
		JP	2001-332547	A	11-30-2001	Toshiba Corp.	ABS
		JP	2001-358225	A	12-26-2001	Agere Systems Guardian Corp.	ABS
		JP	H11-261067	A	09-24-1999	Texas Instruments Inc.	ABS
		JP	2002-060944	A	02-28-2002	IBM Corp.	ABS

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
		M. Koyama et al., "Thermally Stable Ultra-Thin Nitrogen Incorporated ZrO ₂ Gate Dielectric Prepared by Low Temperature Oxidation of ZrN", Technical Digest, IEDM, December 2-5, 2001, pages 459-462.	
		Hag-Ju Cho et al., Novel Nitrogen Profile Engineering for Improved TaN/HfO ₂ /Si MOSFET Performance, IEDM, Technical Digest 2001, pages 655-658.	
		Hag-Ju Cho et al., Structural and Electrical Properties of HfO ₂ with Top Nitrogen Incorporated Layer, IEEE Electron Device Letters, Vol. 23, No. 5, May 2002, pages 249-251.	

Examiner Signature

Date Considered

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